

## Dual N-Channel 30 V (D-S) MOSFET

### PRODUCT SUMMARY

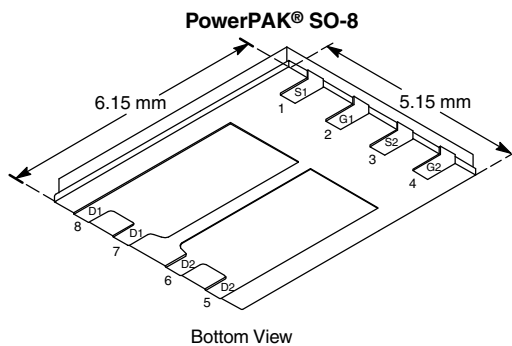
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
30	0.022 at $V_{GS} = 10$ V	10
	0.030 at $V_{GS} = 4.5$ V	8.5

### FEATURES

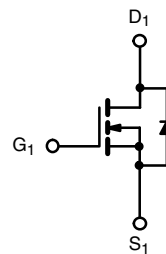
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 %  $R_g$  Tested
- Compliant to RoHS Directive 2002/95/EC



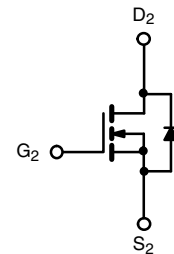
**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available



**Ordering Information:** Si7844DP-T1-E3 (Lead (Pb)-free)  
Si7844DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	$V_{DS}$	30		V
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	10	6.4	A
		8.0	5.1	
Pulsed Drain Current	$I_{DM}$	20		
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	2.9	1.1	
Maximum Power Dissipation <sup>a</sup>	$P_D$	3.5	1.4	W
		2.2	0.9	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) <sup>b, c</sup>		260		

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	26	35	°C/W
		60	85	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	3.9	5.5	

Notes:

- Surface mounted on 1" x 1" FR4 board.
- See solder profile ([www.vishay.com/ppg?73257](http://www.vishay.com/ppg?73257)). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

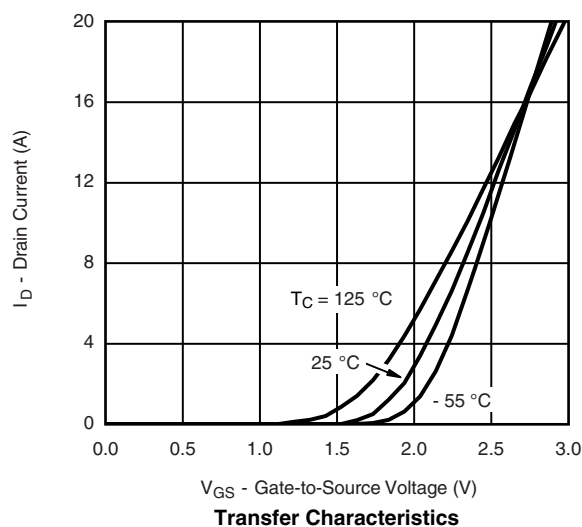
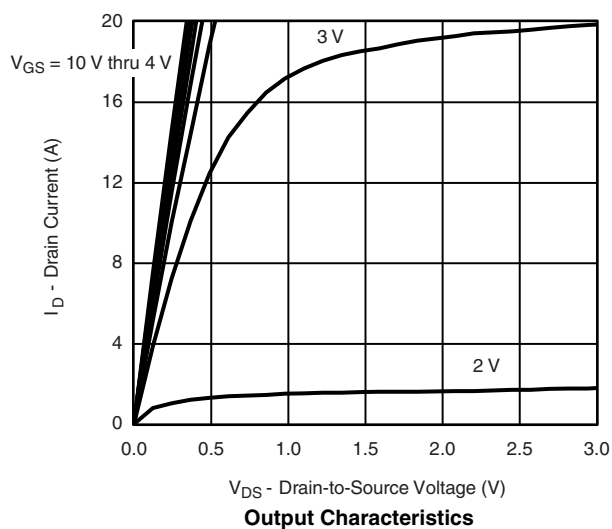
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	0.8		2.4	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 55\text{ }^{\circ}\text{C}$			5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$ , $V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 10\text{ A}$		0.018	0.022	$\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 8.5\text{ A}$		0.024	0.030	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 10\text{ A}$		22		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.9\text{ A}$ , $V_{GS} = 0\text{ V}$		0.75	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 10\text{ A}$		13	20	nC
Gate-Source Charge	$Q_{gs}$			2		
Gate-Drain Charge	$Q_{gd}$			2.7		
Gate Resistance	$R_g$		0.5		3.2	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}$ , $R_L = 15\Omega$ $I_D \cong 1\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 6\Omega$		8	16	ns
Rise Time	$t_r$			10	20	
Turn-Off Delay Time	$t_{d(off)}$			21	40	
Fall Time	$t_f$			10	20	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 2.9\text{ A}$ , $dI/dt = 100\text{ A}/\mu\text{s}$		40	80	

Notes:

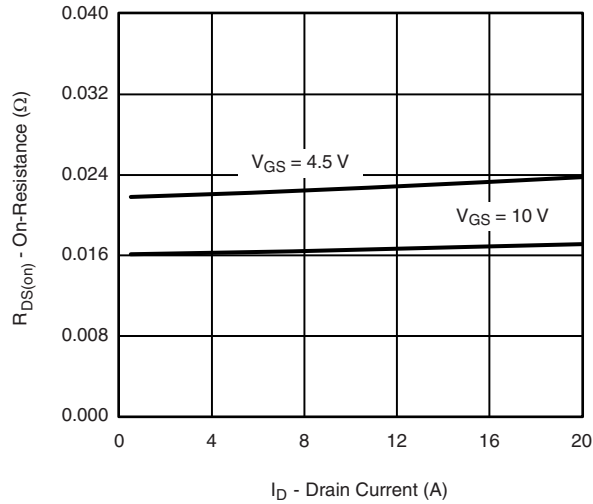
a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

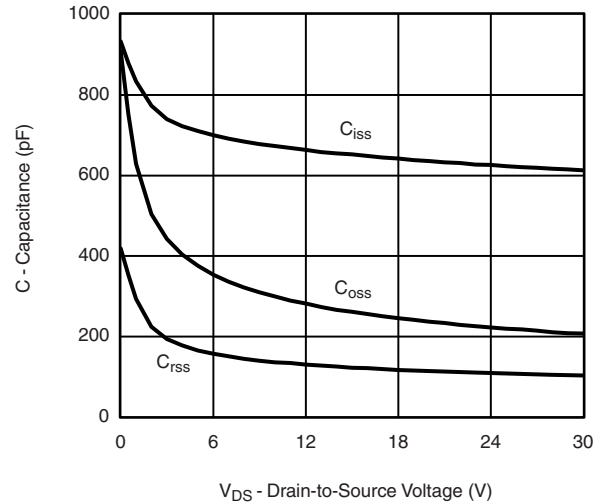
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** ( $25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

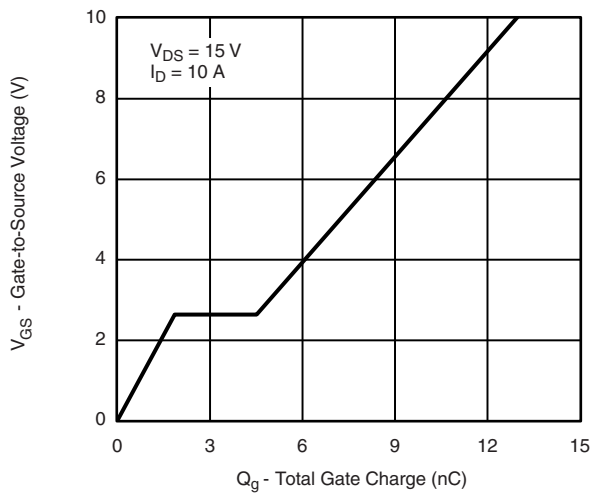
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



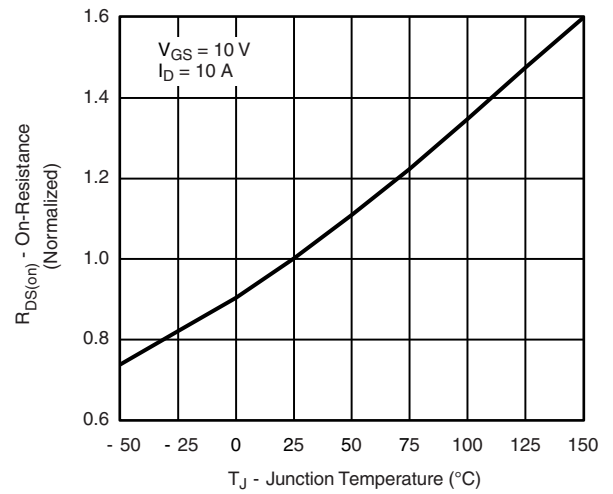
**On-Resistance vs. Drain Current**



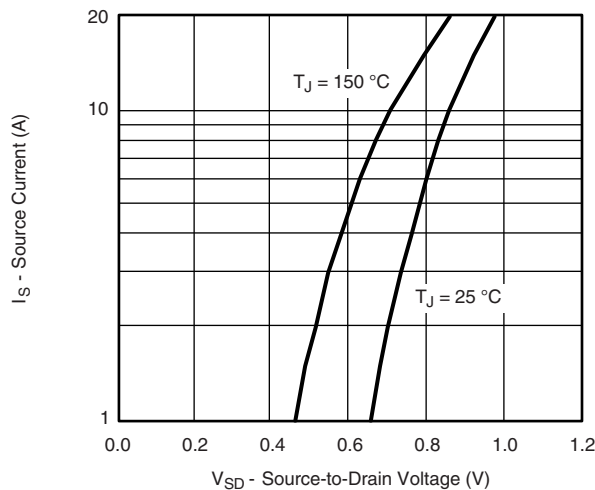
**Capacitance**



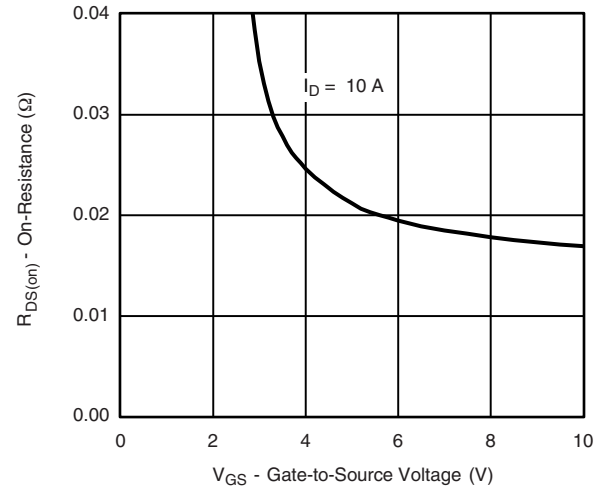
**Gate Charge**



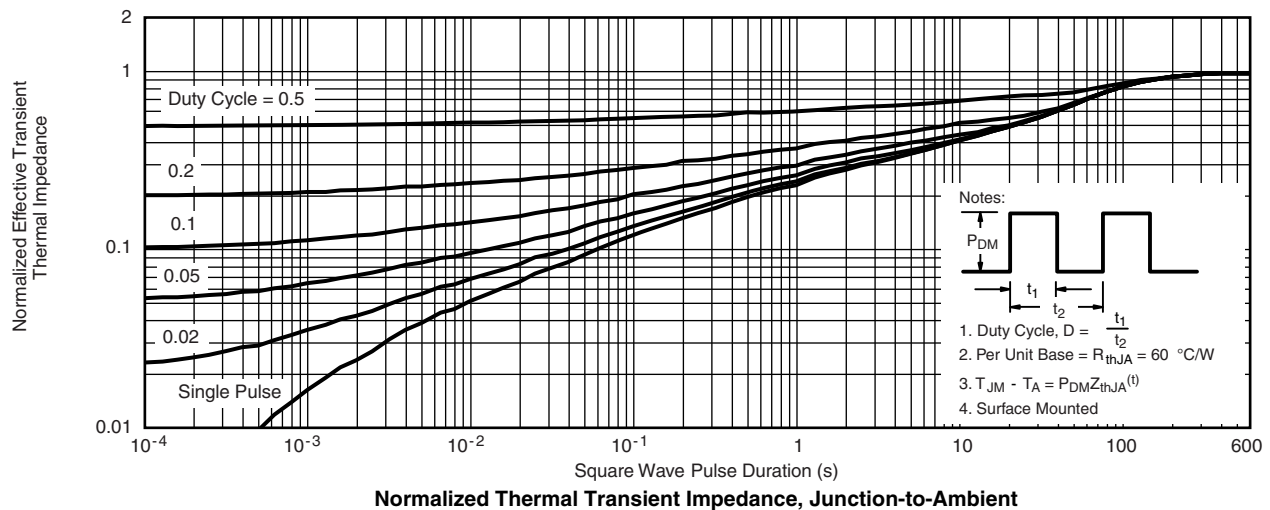
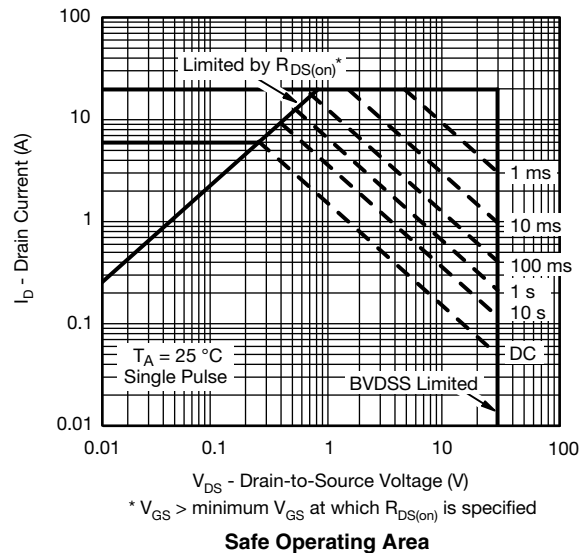
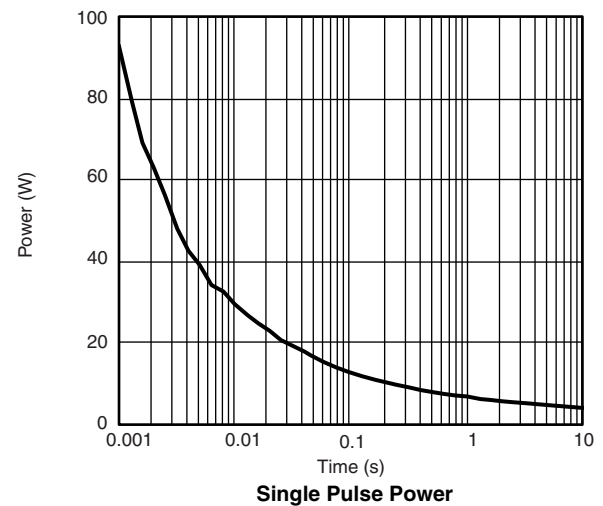
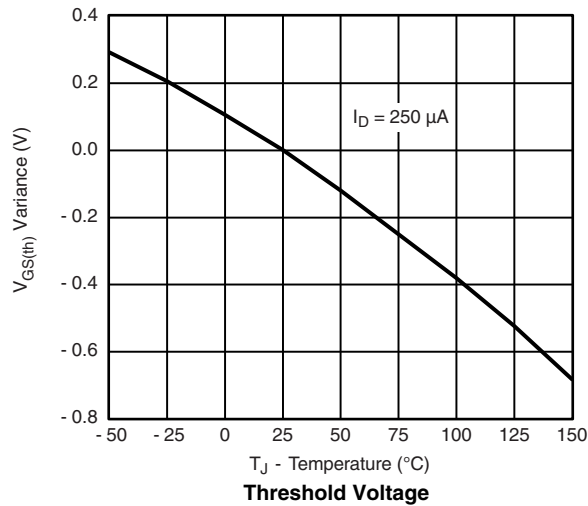
**On-Resistance vs. Junction Temperature**



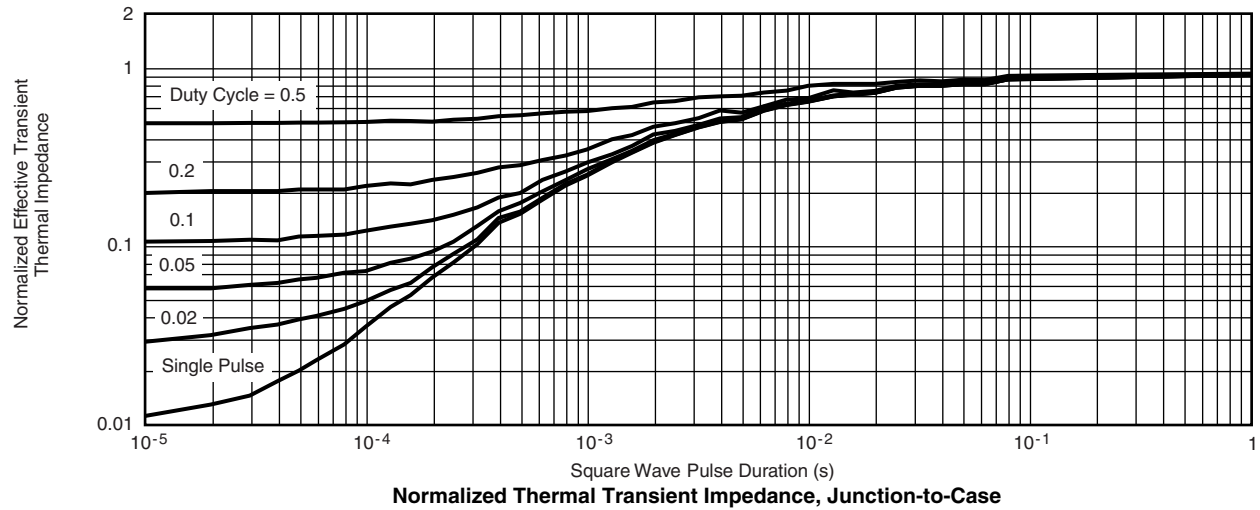
**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

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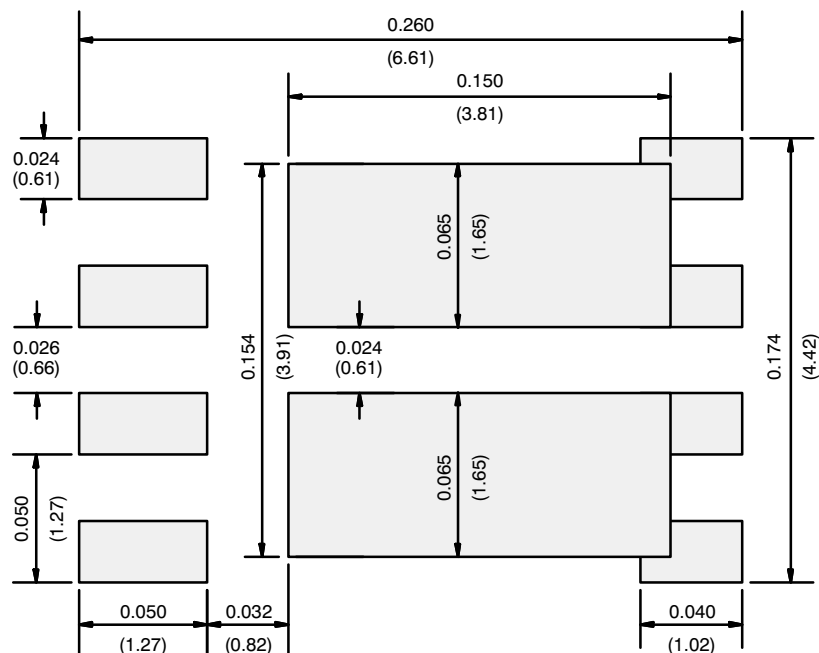
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## PowerPAK® SO-8, (Single/Dual)



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.97	1.04	1.12	0.038	0.041	0.044
A1		-	0.05	0	-	0.002
b	0.33	0.41	0.51	0.013	0.016	0.020
c	0.23	0.28	0.33	0.009	0.011	0.013
D	5.05	5.15	5.26	0.199	0.203	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.56	3.76	3.91	0.140	0.148	0.154
D3	1.32	1.50	1.68	0.052	0.059	0.066
D4	0.57 typ.			0.0225 typ.		
D5	3.98 typ.			0.157 typ.		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	5.79	5.89	5.99	0.228	0.232	0.236
E2 (for AL product)	3.30	3.48	3.66	0.130	0.137	0.144
E2 (for other product)	3.48	3.66	3.84	0.137	0.144	0.151
E3	3.68	3.78	3.91	0.145	0.149	0.154
E4 (for AL product)	0.58 typ.			0.023 typ.		
E4 (for other product)	0.75 typ.			0.030 typ.		
e	1.27 BSC			0.050 BSC		
K (for AL product)	1.45 typ.			0.057 typ.		
K (for other product)	1.27 typ.			0.050 typ.		
K1	0.56	-	-	0.022	-	-
H	0.51	0.61	0.71	0.020	0.024	0.028
L	0.51	0.61	0.71	0.020	0.024	0.028
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
M	0.125 typ.			0.005 typ.		
ECN: C13-0702-Rev. K, 20-May-13						
DWG: 5881						

## RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Dual



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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